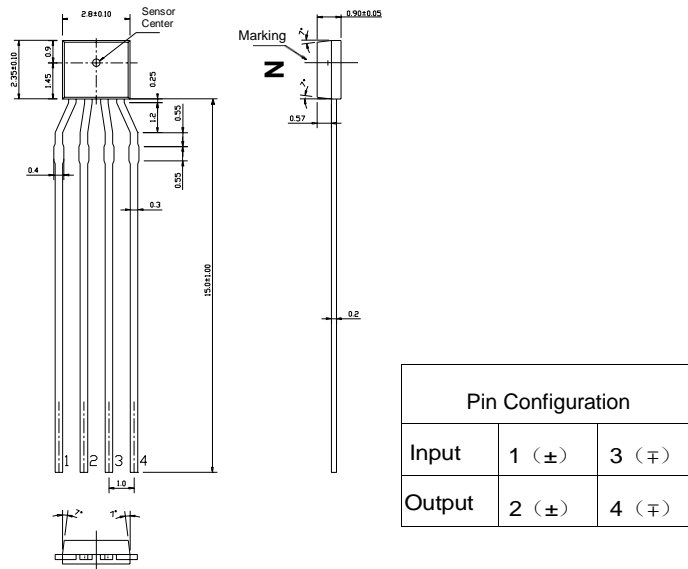


Features

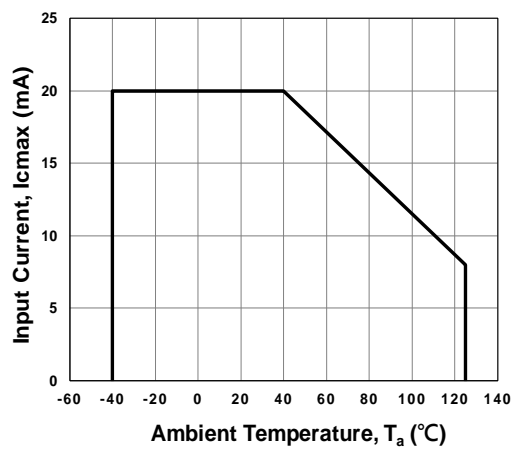
- Ultra High-sensitivity InSb Hall element
- Thin-type SIP Package
- Shipped in Bulk by Pack (500pcs per pack)

Dimensional Drawing (Unit: mm)

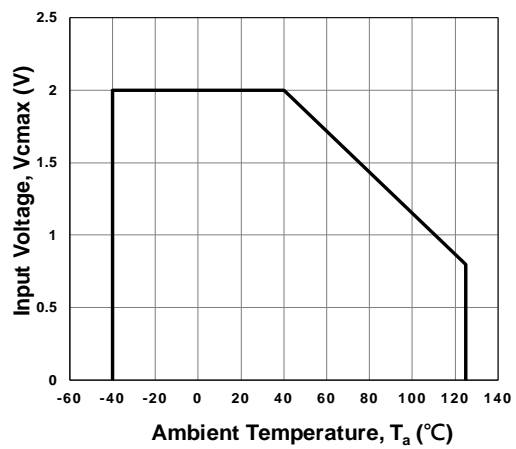


Absolute Maximum Rating

Symbol	Parameter	Rating	Units
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _{opr}	Operating Temperature Range	-40 to 125	°C
I _c	Maximum Input Current	20	mA
V _c	Maximum Input Voltage	2	V



Input Current Detering



Input Voltage Detering

Table 1. Electrical Characteristics (T_a = 25°C)

Item	Symbol	Test Conditions.	Min.	Typ.	Max.	Unit
Hall Voltage	V _H	B = 50mT, V _C =1V	310	---	415	mV
Input Resistance	R _{in}	B = 0mT, I _C = 0.1mA	240	---	550	Ω
Output Resistance	R _{out}	B = 0mT, I _C = 0.1mA	240	---	550	Ω
Offset Voltage	V _{os}	B = 0mT, V _C = 1V	-7	---	+7	mV
Temp. Coeffi. of V _H	αV _H	B = 50mT, I _C = 5mA, T _a = 0°C ~ 40°C	---	-1.8	---	%/°C
Temp. Coeffi. of R _{in}	αR _{in}	B = 0mT, I _C = 0.1mA, T _a = 0°C ~ 40°C	---	-1.8	---	%/°C

Note:

1. $V_H = V_{H-M} - V_{os}$

In which V_{H-M} is the Output Hall Voltage, V_H is the Hall Voltage and V_{os} is the offset Voltage under the identical electrical stimuli.

2. $\alpha V_H = \frac{1}{V_H(T_1)} \times \frac{V_H(T_3) - V_H(T_2)}{(T_3 - T_2)} \times 100$

3. $\alpha R_{in} = \frac{1}{R_{in}(T_1)} \times \frac{R_{in}(T_3) - R_{in}(T_2)}{(T_3 - T_2)} \times 100$

T₁ = 20°C , T₂ = 0°C , T₃ = 40°C

Table 2. Classification of Hall Voltage (V_H)

Rank	V _H [mV]	Conditions
G	310 ~ 370	B=50mT, V _C =1V

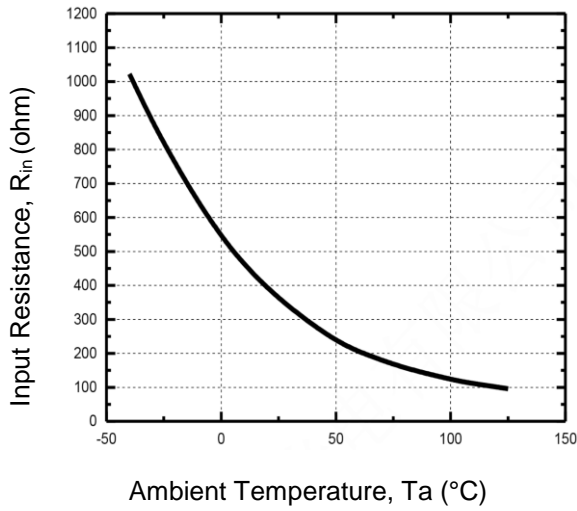


Fig.1 R_{in} - T_a

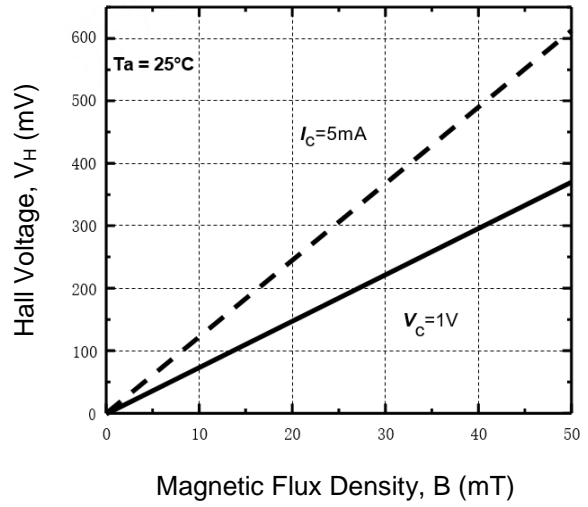


Fig.2 V_H - B

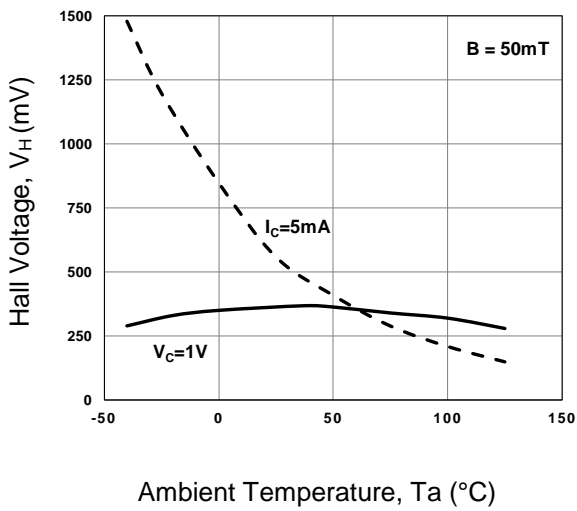


Fig.3 V_H - T_a

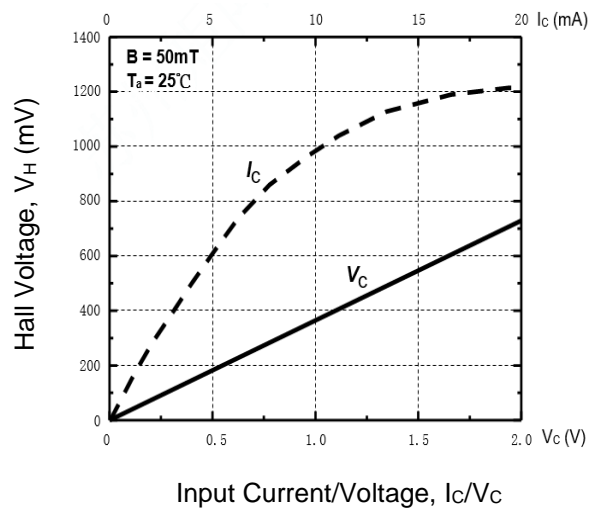


Fig.4 V_H - I_c , V_H - V_c

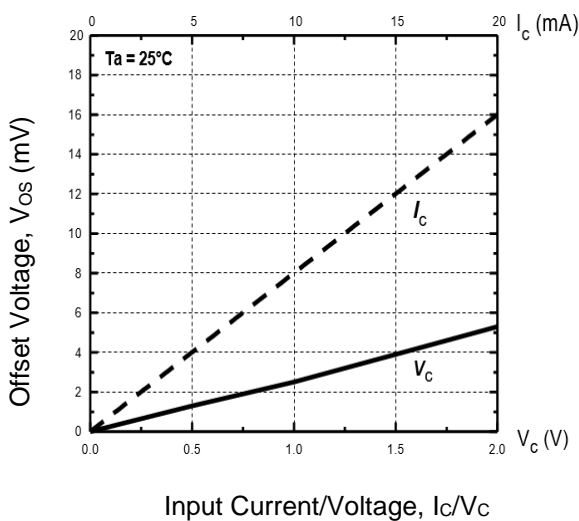


Fig.5 V_{os} - I_c , V_{os} - V_c